

# Giacinta Parish

## List of Publications by Year in descending order

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56  
papers

688  
citations

566801

15  
h-index

610482

24  
g-index

56  
all docs

56  
docs citations

56  
times ranked

725  
citing authors

#	ARTICLE	IF	CITATIONS
1	Surface micromachining multilayer porous silicon for spectral filtering applications. <i>Materials Science in Semiconductor Processing</i> , 2022, 138, 106314.	1.9	7
2	Optimising porous silicon electrical properties for thermal sensing applications. <i>Microporous and Mesoporous Materials</i> , 2021, 312, 110767.	2.2	11
3	pH-Dependent surface charge at the interfaces between aluminum gallium nitride (AlGaN) and aqueous solution revealed by surfactant adsorption. <i>Journal of Colloid and Interface Science</i> , 2021, 583, 331-339.	5.0	4
4	Engineering 1/f noise in porous silicon thin films for thermal sensing applications. <i>Microporous and Mesoporous Materials</i> , 2021, 324, 111302.	2.2	11
5	Dynamic Pressure/Temperature Behaviour of GaN-Based Chemical Sensors. <i>IEEE Sensors Journal</i> , 2021, 21, 18877-18886.	2.4	3
6	Effects of surface oxidation on the pH-dependent surface charge of oxidized aluminum gallium nitride. <i>Journal of Colloid and Interface Science</i> , 2021, 603, 604-614.	5.0	3
7	Vertical carrier transport in strain-balanced InAs/InAsSb type-II superlattice material. <i>Applied Physics Letters</i> , 2020, 116, .	1.5	27
8	Locally-Strain-Induced Heavy-Hole-Band Splitting Observed in Mobility Spectrum of p-Type InAs Grown on GaAs. <i>Physica Status Solidi - Rapid Research Letters</i> , 2020, 14, 1900604.	1.2	8
9	pH-dependent surface properties of the gallium nitride " Solution interface mapped by surfactant adsorption. <i>Journal of Colloid and Interface Science</i> , 2019, 556, 680-688.	5.0	4
10	Compensating porosity gradient to produce flat, micromachined porous silicon structures. <i>Microporous and Mesoporous Materials</i> , 2019, 284, 427-433.	2.2	6
11	Role of GaN cap layer for reference electrode free AlGaN/GaN-based pH sensors. <i>Sensors and Actuators B: Chemical</i> , 2019, 287, 250-257.	4.0	16
12	Density Functional Theory Simulations of Water Adsorption and Activation on the ( $\sim 201$ ) $\text{Ga}_2\text{O}_3$ Surface. <i>Chemistry - A European Journal</i> , 2018, 24, 7445-7455.	1.7	11
13	Optimization of Superlattice Barrier HgCdTe nBn Infrared Photodetectors Based on an NEGF Approach. <i>IEEE Transactions on Electron Devices</i> , 2018, 65, 591-598.	1.6	20
14	Effect of pH and structure on the channel conductivity of AlGaN/GaN heterostructure based sensors. <i>Sensors and Actuators B: Chemical</i> , 2018, 269, 54-61.	4.0	7
15	XPS/NEXAFS spectroscopic and conductance studies of glycine on AlGaN/GaN transistor devices. <i>Applied Surface Science</i> , 2018, 435, 23-30.	3.1	6
16	Released all-porous-silicon microstructure for spectrometer applications. , 2018, , .		0
17	GaSb-based II-VI Semiconductors for Application in Next Generation Infrared Detectors. , 2018, , .		0
18	Theoretical study of the influence of surface effects on GaN-based chemical sensors. <i>Applied Surface Science</i> , 2018, 452, 75-86.	3.1	12

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19	Description of ionophore-doped membranes with a blocked interface. <i>Sensors and Actuators B: Chemical</i> , 2017, 250, 499-508.	4.0	16
20	X-Ray Reciprocal Space Mapping of MBE Grown HgCdTe on Alternative Substrates. <i>Crystal Research and Technology</i> , 2017, 52, 1700167.	0.6	5
21	Ca <sup>2+</sup> detection utilising AlGaIn/GaN transistors with ion-selective polymer membranes. <i>Analytica Chimica Acta</i> , 2017, 987, 105-110.	2.6	36
22	Mercury(II) selective sensors based on AlGaIn/GaN transistors. <i>Analytica Chimica Acta</i> , 2016, 943, 1-7.	2.6	71
23	Superlattice Barrier HgCdTe nBn Infrared Photodetectors: Validation of the Effective Mass Approximation. <i>IEEE Transactions on Electron Devices</i> , 2016, 63, 4811-4818.	1.6	20
24	Effect of CdS Processing Conditions on the Properties of CdS/Si Diodes and CdS/CdTe Thin-Film Solar Cells. <i>IEEE Journal of Photovoltaics</i> , 2015, 5, 1783-1790.	1.5	6
25	Substrate heating effects on properties of CdS thin films prepared by thermal evaporation for photovoltaic applications. , 2015, , .		1
26	Stress control of porous silicon films for microelectromechanical systems. <i>Microporous and Mesoporous Materials</i> , 2015, 218, 88-94.	2.2	17
27	Theoretical Study of Midwave Infrared HgCdTe nBn Detectors Operating at Elevated Temperatures. <i>Journal of Electronic Materials</i> , 2015, 44, 3044-3055.	1.0	19
28	Method to Predict and Optimize Charge Sensitivity of Ungated AlGaIn/GaN HEMT-Based Ion Sensor Without Use of Reference Electrode. <i>IEEE Sensors Journal</i> , 2015, 15, 5320-5326.	2.4	13
29	Investigation of crystallized germanium thin films and germanium/silicon heterojunction devices for optoelectronic applications. <i>Materials Science in Semiconductor Processing</i> , 2015, 30, 413-419.	1.9	9
30	Stress control of porous silicon film for microelectromechanical systems. , 2014, , .		1
31	Synchrotron-based XPS studies of AlGaIn and GaN surface chemistry and its relationship to ion sensor behaviour. <i>Applied Surface Science</i> , 2014, 314, 850-857.	3.1	35
32	Evidence of Sub-Band Modulated Transport in Planar Fully Depleted Silicon-on-Insulator MOSFETs. <i>IEEE Electron Device Letters</i> , 2014, 35, 1082-1084.	2.2	9
33	Released micromachined beams utilizing laterally uniform porosity porous silicon. <i>Nanoscale Research Letters</i> , 2014, 9, 426.	3.1	6
34	Nitrate ion detection using AlGaIn/GaN heterostructure-based devices without a reference electrode. <i>Sensors and Actuators B: Chemical</i> , 2013, 181, 301-305.	4.0	37
35	Surface Morphology Control of Passivated Porous Silicon Using Reactive Ion Etching. <i>Journal of Microelectromechanical Systems</i> , 2012, 21, 756-761.	1.7	11
36	Multilayer porous silicon diffraction gratings operating in the infrared. <i>Nanoscale Research Letters</i> , 2012, 7, 645.	3.1	15

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37	Phonon limited transport in graphene nanoribbon field effect transistors using full three dimensional quantum mechanical simulation. Journal of Applied Physics, 2012, 112, 094505.	1.1	25
38	Modeling and Design of a Thin-Film CdTe/Ge Tandem Solar Cell. Journal of Electronic Materials, 2012, 41, 2759-2765.	1.0	2
39	Development of an Alkaline-Compatible Porous-Silicon Photolithographic Process. Journal of Microelectromechanical Systems, 2011, 20, 418-423.	1.7	32
40	Transport Studies of AlGaIn/GaN Heterostructures of Different Al Mole Fractions With Variable $\text{SiN}_x$ Passivation Stress. IEEE Transactions on Electron Devices, 2011, 58, 2589-2596.	1.6	18
41	Implantation angle periphery effects on non-alloyed Si-implanted ohmic contacts for AlGaIn/GaN high electron mobility transistors. Solid-State Electronics, 2011, 56, 56-59.	0.8	0
42	Reactive ion etching of porous silicon for MEMS applications. , 2010, , .		1
43	Ion versus pH sensitivity of ungated AlGaIn/GaN heterostructure-based devices. Applied Physics Letters, 2010, 97, .	1.5	35
44	Cell growth and attachment to AlGaIn surfaces for biosensor applications. , 2010, , .		2
45	Localised defect-induced Schottky barrier lowering in n-GaN Schottky diodes. Solid-State Electronics, 2008, 52, 171-174.	0.8	8
46	Effect of MBE Growth Conditions on Multiple Electron Transport in InN. Journal of Electronic Materials, 2008, 37, 593-596.	1.0	12
47	Multiple carrier transport in n-face indium nitride. Physica Status Solidi (B): Basic Research, 2008, 245, 907-909.	0.7	5
48	Characterisation of multiple carrier transport in indium nitride grown by molecular beam epitaxy. Physica Status Solidi C: Current Topics in Solid State Physics, 2007, 4, 2423-2427.	0.8	11
49	Characterisation of Electron Transport in MBE Grown Indium Nitride. , 2006, , .		0
50	Determination of diffusion length of p-type GaN from spectral-response measurements. , 2006, , .		1
51	Characterisation of Multiple Carrier Transport in Indium Nitride Grown by Molecular Beam Epitaxy. Japanese Journal of Applied Physics, 2006, 45, L1090-L1092.	0.8	43
52	Investigations of ohmic contacts to reactive ion-etched p-type GaN. , 2004, , .		2
53	Magnetoresistance characteristics of gamma-irradiated Al 0.35 Ga 0.65 N/GaN HFETs. , 2004, 5274, 152.		0
54	<title>60Co gamma-irradiation-induced defects in MOCVD n-GaN</title>. , 2001, , .		1

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55	Simple wet etching of GaN. , 2001, , .		5
56	<title>Anomalous drain current-voltage characteristics in AlGaIn/GaN MODFETs at low temperatures</title>. , 1999, , .		2